

Vishay Siliconix

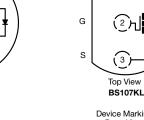
RoHS

COMPLIANT

HALOGEN FREE

N-Channel 240 V (D-S) MOSFET

TO-226AA (TO-92) S G 2 Top View TN2404KL





"S" TN 2404KL xxyy "S" = Siliconix Logo xxyy = Date Code

ORDERING INFORMATION

Lead (Pb)-free and halogen-free

Alternate manufacturing location

Package Lead (Pb)-free

Tape and Reel

Device Marking
Front View

TO-92-18RM

(TO-18 Lead Form)

"S" BS 107KL xxyy	"S" = Siliconix Log xxyy = Date Code
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TO-236 (SOT-23)

TN2404K-T1-E3

TN2404K-T1-GE3

TN2404K-T1-BE3

PRODUCT SUMMARY				
PART NUMBER	TN2404K	TN2404K, BS107KL		
V _{DS} (V)	24	40		
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10 \text{ V}$	4	4		
Q _g typ. (nC)	4.	87		
I _D (A) ^{a, e}	0.2	0.3		
Configuration	Single			

FEATURES

- Low on-resistance: 4 W
- Secondary breakdown free: 260 V
- Low power / voltage driven
- · Low input and output leakage
- Excellent thermal stability
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

APPLICATIONS

- High-voltage drivers: relays, solenoids, lamps, hammers, displays, transistors, etc.
- Telephone mute switches, ringer circuits
- Power Supply, Converters
- Motor Control

TO-236 (SOT-23)

K1 = Part Number Code for TN2404K

BENEFITS

- · Low offset voltage
- Full-voltage operation

TO-226AA (TO-92)

TN2404KL-TR1-E3

- Easily driven without buffer
- Low error voltage
- No high-temperature "Run-Away"

Rui	n-Away''
	TO-92-18RM (TO-18 Lead Form)

BS107KL-TR1-E3

Marking Code: K1ywl

y = Year Code

w = Week Code I = Lot Traceability

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ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
PARAMETER		SYMBOL	TN2404K	TN2404KL/BS107KL	SYMBOL	
Drain-source voltage	ource voltage V _{DS} 240		40	V		
Gate-source voltage		V _{GS}	± 20] v	
Continuous drain current (T _J = 150 °C)	T _A = 25 °C	- I _D	0.2	0.3		
	T _A = 70 °C		0.16	0.25	Α	
Pulsed drain current (t = 300 μs)		I _{DM}	0.8	1.4		
Maximum power dissipation	T _A = 25 °C	- P _D	0.36	0.8	W	
	T _A = 70 °C		0.23	0.51	VV	
Thermal resistance junction-to-ambient		R _{thJA}	350b	156	°C/W	
Operating junction and storage temperature range		T _J , T _{stg}	- 55 to 150		°C	

Notes

- a. Pulse width limited by maximum junction temperature
- b. Surface mounted on an FR4 board

PARAMETER	SYMBOL	TEST CONDITIONS		LIMITS			
PANAIVIE I EN	STWIBOL	TEST CONDITIONS	MIN.	TYP. a	MAX.	UNIT	
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 100 \mu\text{A}$	240	257	-	V	
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$		1.65	2	V	
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
Zero gate voltage drain current		$V_{DS} = 192 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1		
Zero gate voltage drain current	I _{DSS}	V _{DS} = 192 V, V _{GS} = 0 V, T _J = 55 °C	-	-	10	μA	
On state due in accurant 8	,	V _{DS} = 10 V, V _{GS} = 10 V	0.8	-	-	Α	
On-state drain current ^a	I _{D(on)}	V _{DS} = 10 V, V _{GS} = 4.5 V	0.5	-	-		
		$V_{GS} = 10 \text{ V}, I_D = 0.3 \text{ A}$	-	2.2	4		
Drain-source on-state resistance a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 0.2 \text{ A}$	-	2.3	4	W	
		$V_{GS} = 2.5 \text{ V}, I_D = 0.1 \text{ A}$	-	2.4	6	1	
Forward transconductance a	9 _{fs}	V _{DS} = 10 V, I _D = 0.3 A - 1		1.6	-	S	
Diode forward voltage	V _{SD}	$V_{GS} = 0 \text{ V}, I_S = 0.3 \text{ A}$	-	0.8	1.2	V	
Dynamic ^b	·						
Total gate charge	Q_g		-	4.87	8		
Gate-source charge	Q _{gs}	$V_{DS} = 192 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 0.5 \text{ A}$	-	0.56	-	nC	
Gate-drain charge	Q _{gd}		-	1.53	-		
Turn-on delay time	t _{d(on)}		-	5	10		
Rise time	t _r	$V_{DD} = 60 \text{ V}, R_1 = 200 \Omega$	-	12	20	1	
Turn-off delay time	t _{d(off)}	$I_D \cong 0.3 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 25 \Omega$	-	35	60	ns	
Fall time	t _f			16	25		

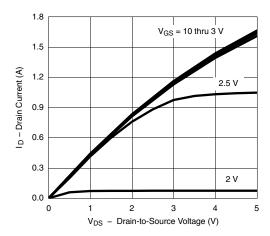
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing

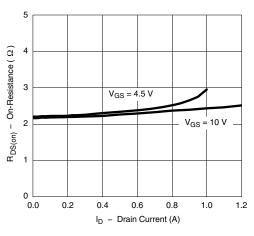
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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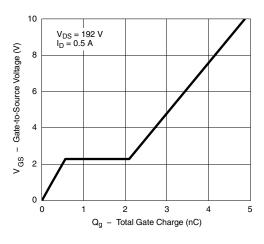
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



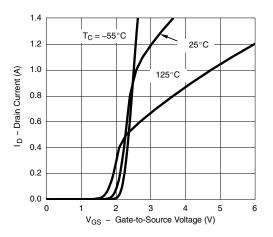
Output Characteristics



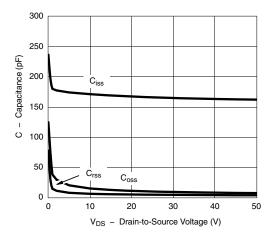
On-Resistance vs. Drain Current



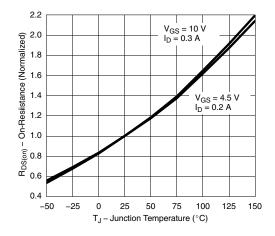
Gate Charge



Transfer Characteristics



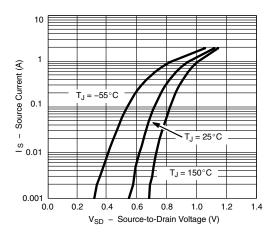
Capacitance

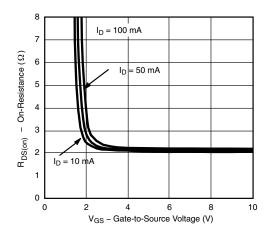


On-Resistance vs. Junction Temperature

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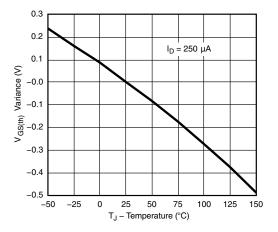
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





Source-Drain Diode Forward Voltage

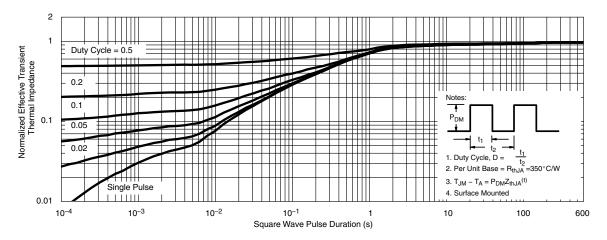
On-Resistance vs. Gate-to-Source Voltage



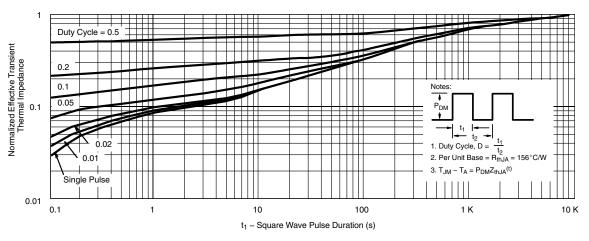
Threshold Voltage

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient (TO-236, TN2404K only)



Normalized Thermal Transient Impedance, Junction-to-Ambient (TO-226AA, TN2404KL and TO-92-18RM, BS107KL only)

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72225.

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SOT-23 (TO-236): 3-LEAD







Dim	MILLI	METERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.037	4 Ref	
e ₁	1.9	0 BSC	0.074	8 Ref	
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.5	50 Ref 0.020 Ref) Ref	
q	3°	8°	3°	8°	
FCN: S-03946-Rev K 09-	lul-01	•			

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DWG: 5479

Document Number: 71196 www.vishay.com 09-Jul-01



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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